

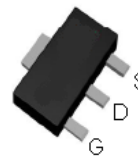
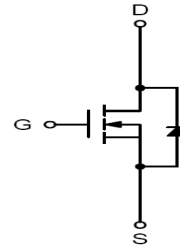
The 3401 uses advanced trench technology to provide excellent  $R_{DS(ON)}$  and low gate charge. This device is suitable for use as a load switch or in PWM applications.

## GENERAL FEATURES

- $R_{DS(ON)} < 70\text{m}\Omega$  @  $V_{GS} = -4.5\text{V}$   
 $R_{DS(ON)} < 60\text{m}\Omega$  @  $V_{GS} = -10\text{V}$
- High Power and current handling capability
- Lead free product is acquired
- Surface Mount Package

## Application

- PWM applications
- Load switch
- Power management



Top View SOT-89

ABSOLUTE MAXIMUM RATINGS( $T_A=25^\circ\text{C}$  unless otherwise noted)

Symbol	Parameter	Rating	Unit
<b>Common Ratings (<math>T_C=25^\circ\text{C}</math> Unless Otherwise Noted)</b>			
$V_{GS}$	Gate-Source Voltage	$\pm 12$	V
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	-30	V
$T_J$	Maximum Junction Temperature	175	$^\circ\text{C}$
$T_{STG}$	Storage Temperature Range	-50 to 150	$^\circ\text{C}$
$I_S$	Diode Continuous Forward Current <sup>①</sup>	$T_C=25^\circ\text{C}$ -4.2	A
$I_{DM}$	Pulse Drain Current Tested <sup>①</sup>	$T_C=25^\circ\text{C}$ -16	A
$I_D$	Continuous Drain Current( $V_{GS}=-10\text{V}$ ) <sup>①</sup>	$T_C=25^\circ\text{C}$ -4.2	A

## ELECTRICAL CHARACTERISTICS (T<sub>A</sub>=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>OFF CHARACTERISTICS</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =-250UA	-30			V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-24V, V <sub>GS</sub> =0V			1	μ A
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±12V, V <sub>DS</sub> =0V			±100	nA
<b>ON CHARACTERISTICS (Note 3)</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250UA	-0.6		-1.8	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =-10V I <sub>D</sub> =-4A		46		mΩ
		V <sub>GS</sub> =-4.5V I <sub>D</sub> =-2A		52		mΩ
<b>DYNAMIC CHARACTERISTICS (Note4)</b>						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =-15V, V <sub>GS</sub> =0V, F=1.0MHZ		580		PF
Output Capacitance	C <sub>oss</sub>			125		PF
Reverse Transfer Capacitance	C <sub>rss</sub>			85		PF
<b>SWITCHING CHARACTERISTICS (Note 4)</b>						
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> =-15V, I <sub>D</sub> =-1A, R <sub>GEN</sub> =6 , V <sub>GEN</sub> =-10V, R <sub>L</sub> =15		10		nS
Turn-on Rise Time	t <sub>r</sub>			10		nS
Turn-Off Delay Time	t <sub>d(off)</sub>			36		nS
Turn-Off Fall Time	t <sub>f</sub>			25		nS
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =-15V, I <sub>D</sub> =-5.5A, V <sub>GS</sub> =-10V		12		nC
Gate-Source Charge	Q <sub>gs</sub>	V <sub>DS</sub> =-15V, I <sub>D</sub> =-5.5A, V <sub>GS</sub> =-4.5V		2		nC
Gate-Drain Charge	Q <sub>gd</sub>	V <sub>DS</sub> =-15V, I <sub>D</sub> =-5.5A, V <sub>GS</sub> =-10V		3		nC
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =-1A		-0.8	-1.3	V

## NOTES:

- Surface Mounted on FR4 Board, t ≤ 10 sec.
- Pulse Test : Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.
- Guaranteed by design, not subject to production testing.

## TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

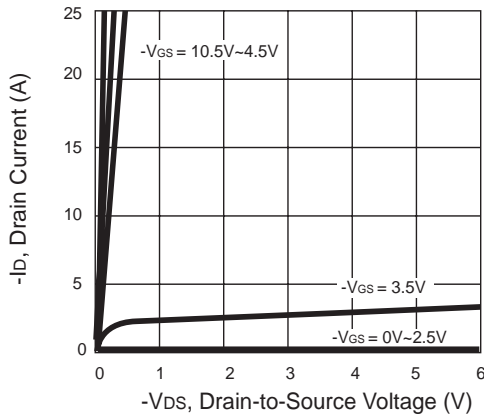


Figure 1. Output Characteristics

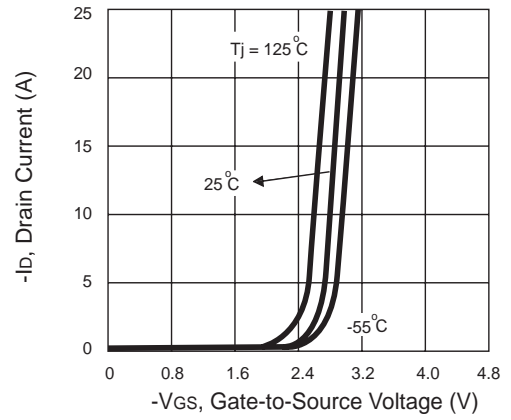


Figure 2. Transfer Characteristics

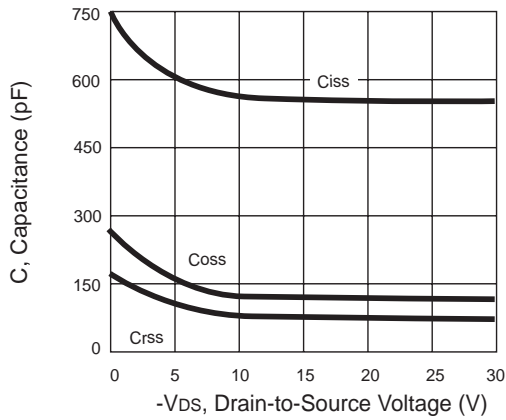


Figure 3. Capacitance

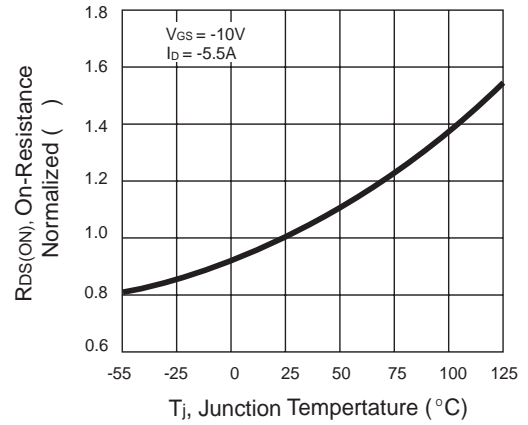


Figure 4. On-Resistance Variation with Temperature

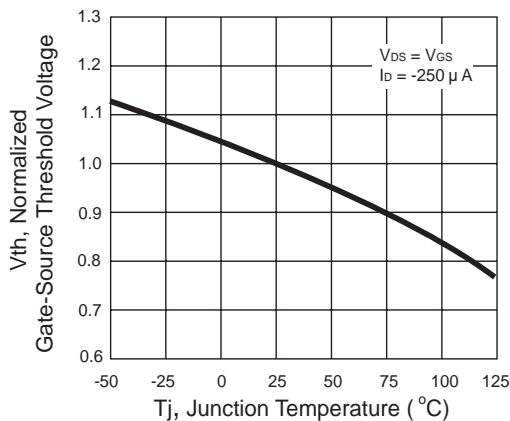


Figure 5. Gate Threshold Variation with Temperature

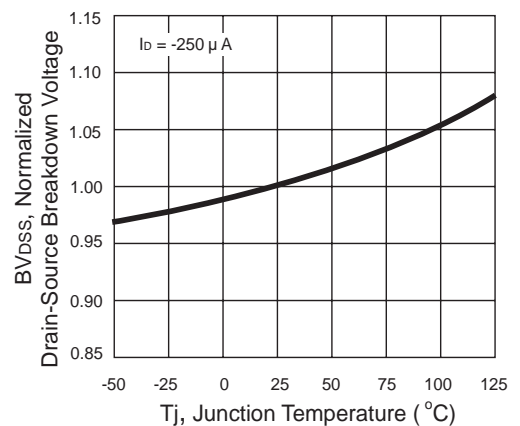


Figure 6. Breakdown Voltage Variation with Temperature

## TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

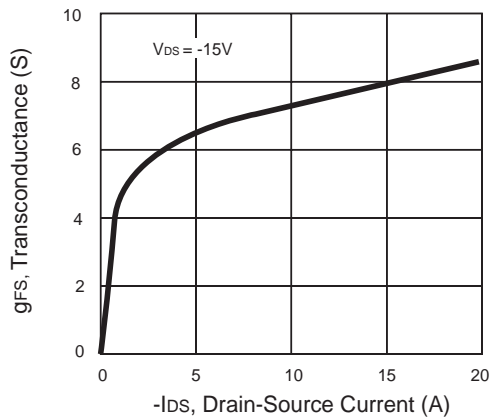


Figure 7. Transconductance Variation with Drain Current

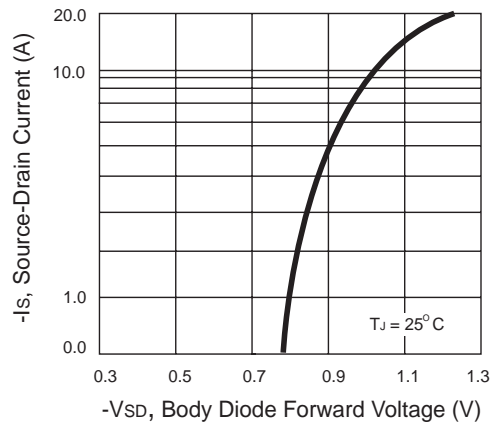


Figure 8. Body Diode Forward Voltage Variation with Source Current

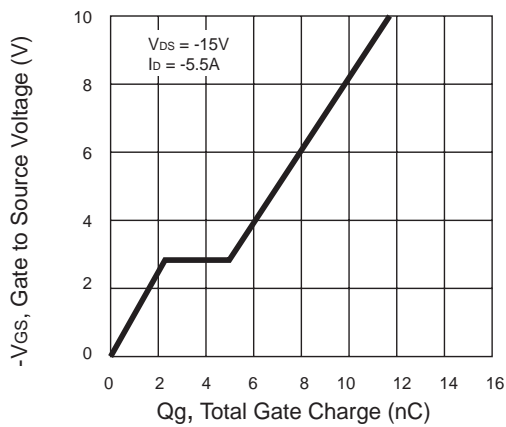


Figure 9. Gate Charge

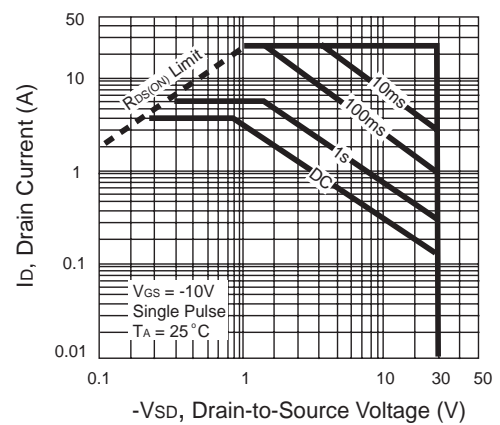


Figure 10. Maximum Safe Operating Area

## TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

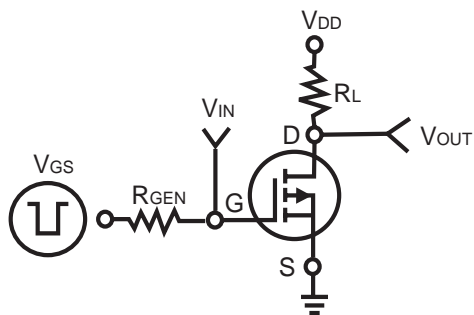


Figure 11. Switching Test Circuit

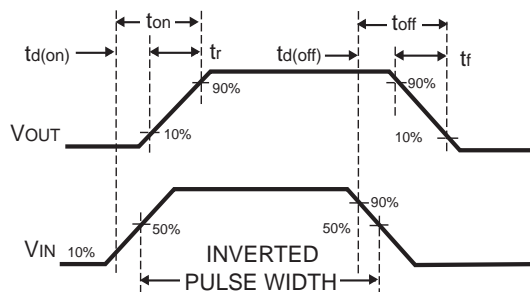


Figure 12. Switching Waveforms

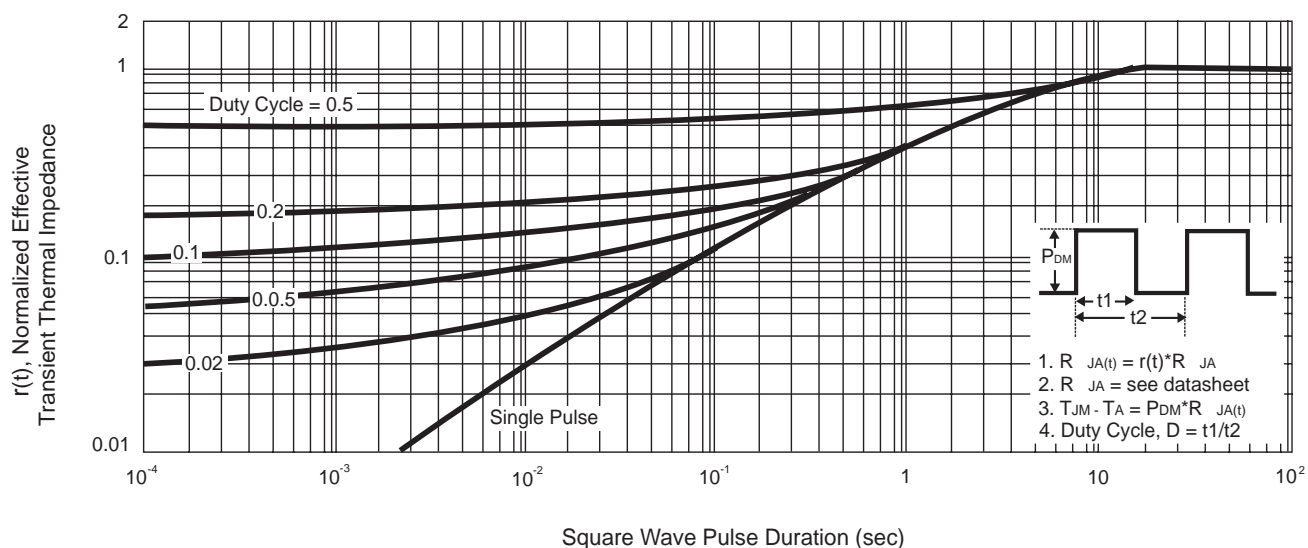
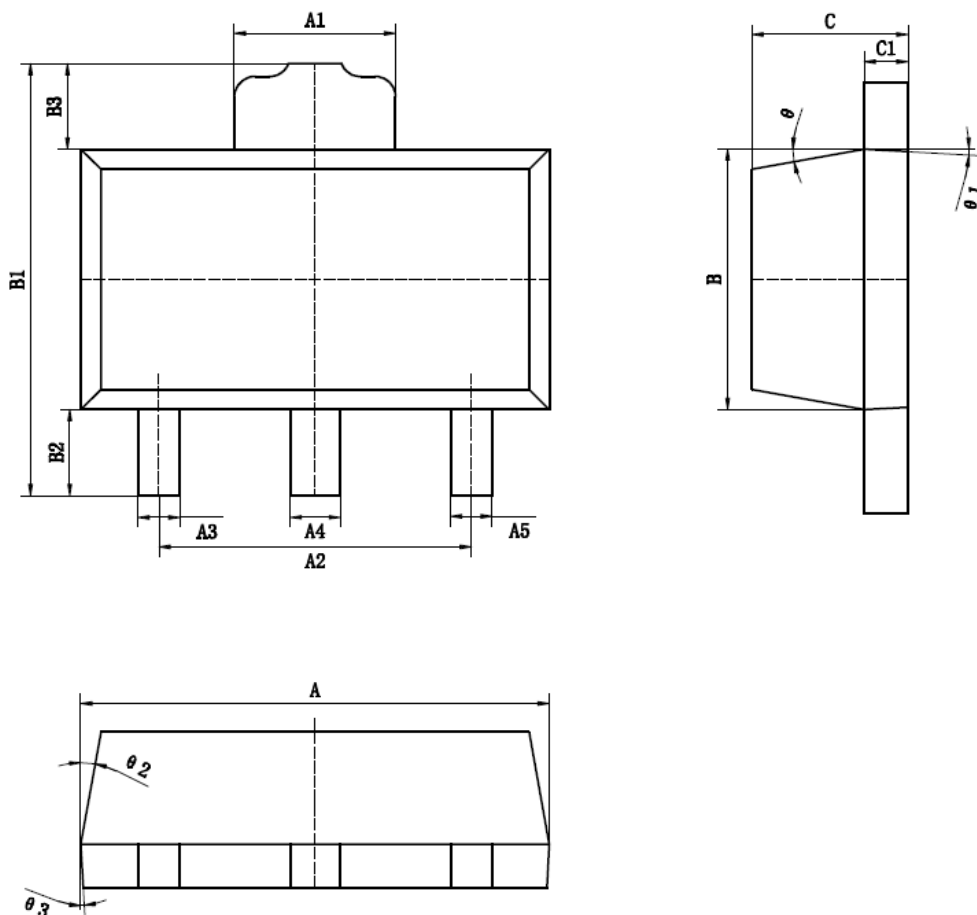


Figure 13. Normalized Thermal Transient Impedance Curve

## Package Information

SOT89-3 Package



标注	尺寸	最小(mm)	最大(mm)	标注	尺寸	最小(mm)	最大(mm)
A		4.40	4.60	B3		0.82	0.83
A1		1.65	1.75	C		1.40	1.60
A2		2.95	3.05	C1		0.35	0.45
A3		0.35	0.45	$\theta$		6° TYP4	
A4		0.43	0.53	$\theta 1$		3° TYP4	
A5		0.35	0.45	$\theta 2$		6° TYP4	
B		2.40	2.60	$\theta 3$		3° TYP4	
B1		4.05	4.25				
B2		0.82	0.83				